

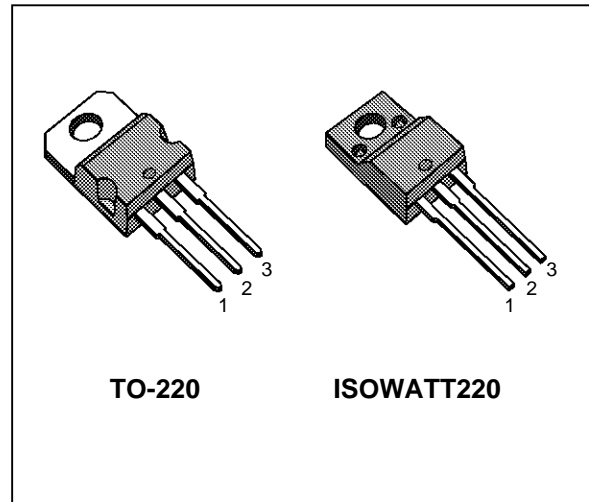
N - CHANNEL ENHANCEMENT MODE POWER MOS TRANSISTORS

TYPE	V _{DSS}	R _{DS(on)}	I _D
BUZ11	50 V	< 0.04 Ω	36 A
BUZ11FI	50 V	< 0.04 Ω	21 A

- TYPICAL R_{DS(on)} = 0.03 Ω
- AVALANCHE RUGGED TECHNOLOGY
- 100% AVALANCHE TESTED
- REPETITIVE AVALANCHE DATA AT 100°C
- LOW GATE CHARGE
- HIGH CURRENT CAPABILITY
- 175°C OPERATING TEMPERATURE

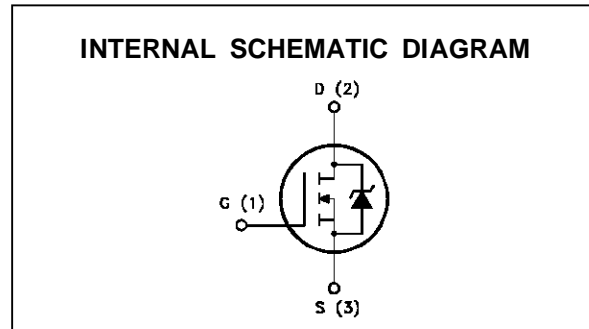
APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SOLENOID AND RELAY DRIVERS
- REGULATORS
- DC-DC & DC-AC CONVERTERS
- MOTOR CONTROL, AUDIO AMPLIFIERS
- AUTOMOTIVE ENVIRONMENT (INJECTION, ABS, AIR-BAG, LAMPDRIVERS, Etc.)



TO-220

ISOWATT220



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		BUZ11	BUZ11FI	
V _{DS}	Drain-source Voltage (V _{GS} = 0)	50		V
V _{DGR}	Drain- gate Voltage (R _{GS} = 20 kΩ)	50		V
V _{GS}	Gate-source Voltage	± 20		V
I _D	Drain Current (continuous) at T _c = 25 °C	36	21	A
I _{DM}	Drain Current (pulsed)	144	144	A
P _{tot}	Total Dissipation at T _c = 25 °C	120	40	W
V _{ISO}	Insulation Withstand Voltage (DC)	—	2000	V
T _{stg}	Storage Temperature	-65 to 175		°C
T _j	Max. Operating Junction Temperature	175		°C
	DIN Humidity Category (DIN 40040)	E		
	IEC Climatic Category (DIN IEC 68-1)	55/150/56		

BUZ11/FI

THERMAL DATA

			TO-220	ISOWATT220	
R _{thj-case}	Thermal Resistance Junction-case	Max	1.25	3.75	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	62.5		°C/W

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Value	Unit
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max, δ < 1%)	36	A
E _{AS}	Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 25 V)	240	mJ
E _{AR}	Repetitive Avalanche Energy (pulse width limited by T _j max, δ < 1%)	60	mJ
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive (T _c = 100 °C, pulse width limited by T _j max, δ < 1%)	25	A

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 μA V _{GS} = 0	50			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating T _j = 125 °C			250 1000	μA μA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 20 V			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} I _D = 1 mA	2.1	3	4	V
R _{DSON}	Static Drain-source On Resistance	V _{GS} = 10V I _D = 18 A		0.03	0.04	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (*)	Forward Transconductance	V _{DS} = 15 V I _D = 18 A	10	16		S
C _{iss} C _{oss} C _{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V _{DS} = 25 V f = 1 MHz V _{GS} = 0		1130 480 140	1500 650 200	pF pF pF

SWITCHING

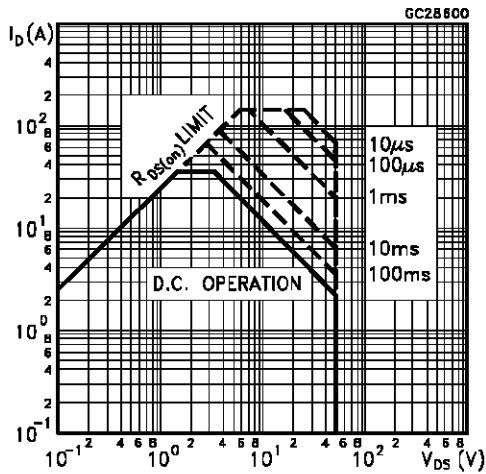
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
t _{d(on)} t _r t _{d(off)} t _f	Turn-on Time Rise Time Turn-off Delay Time Fall Time	V _{DD} = 30 V I _D = 3 A R _{GS} = 50 Ω V _{GS} = 10 V		40 145 220 135	60 210 320 200	ns ns ns ns

ELECTRICAL CHARACTERISTICS (continued)
SOURCE DRAIN DIODE

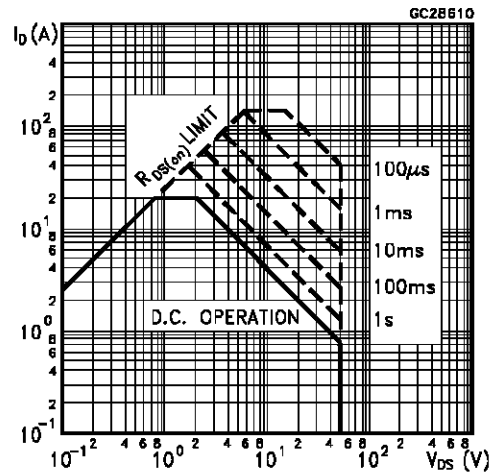
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				36	A
I_{SDM}	Source-drain Current (pulsed)				144	A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 72 \text{ A}$ $V_{GS} = 0$			2.2	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 36 \text{ A}$ $V_{DD} = 30 \text{ V}$ $di/dt = 100 \text{ A}/\mu\text{s}$ $T_j = 150 \text{ }^\circ\text{C}$		90		ns
Q_{rr}	Reverse Recovery Charge			0.2		μC

(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

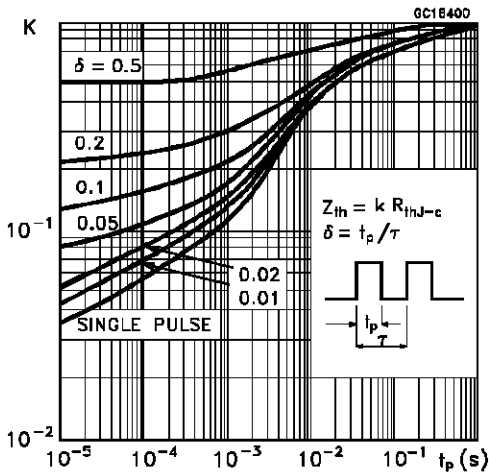
Safe Operating Area For TO-220



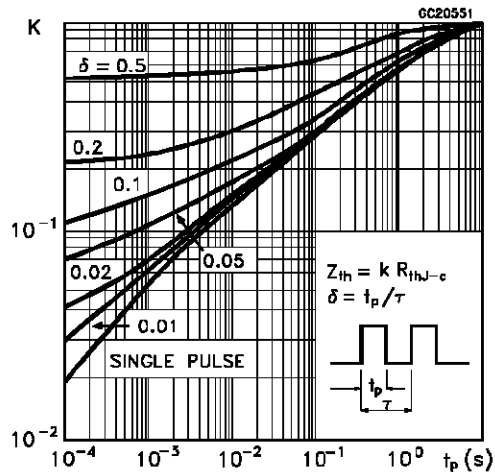
Safe Operating Area For ISOWATT220



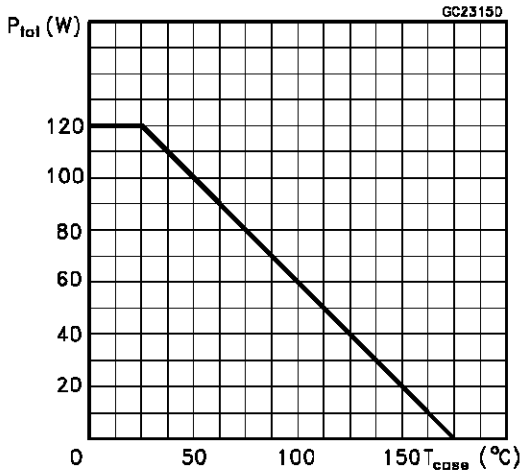
Thermal Impedance For TO-220



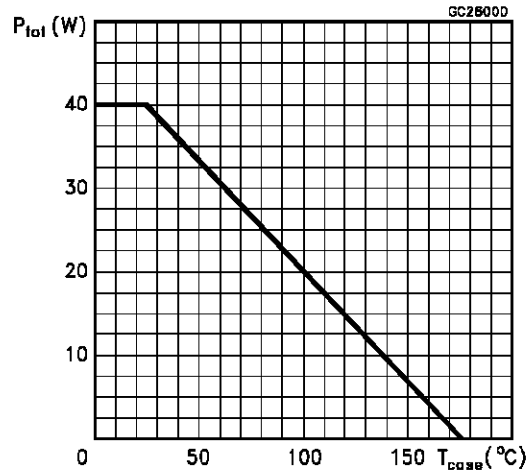
Thermal Impedance For ISOWATT220



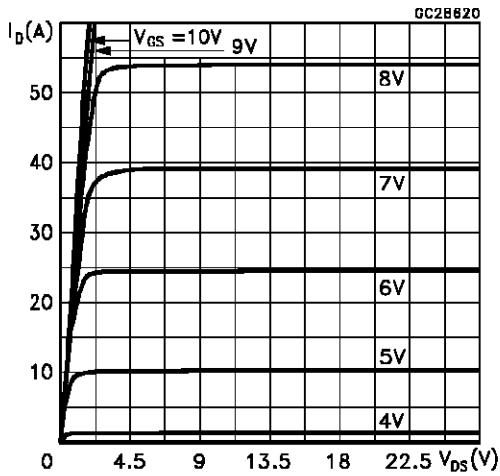
Derating Curve For TO-220



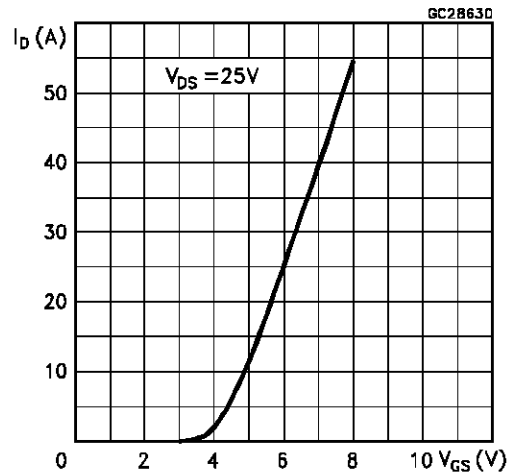
Derating Curve For ISOWATT220



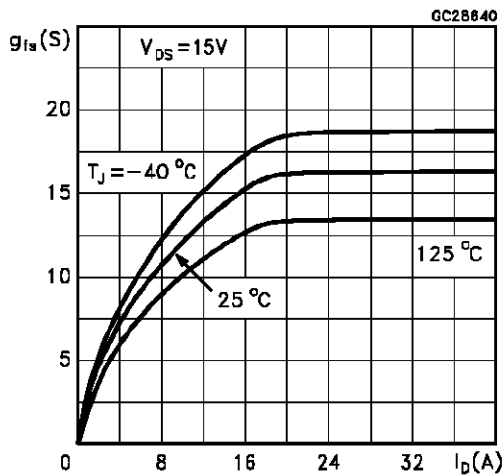
Output Characteristics



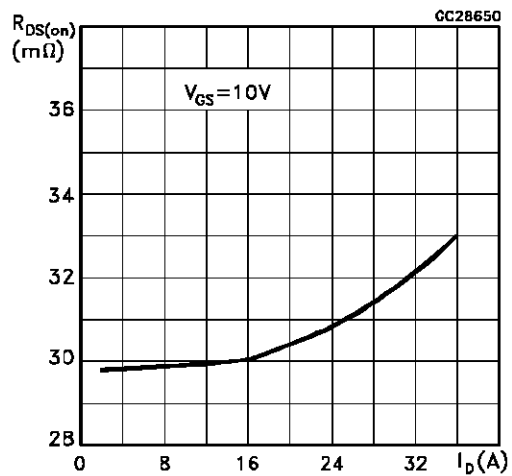
Transfer Characteristics



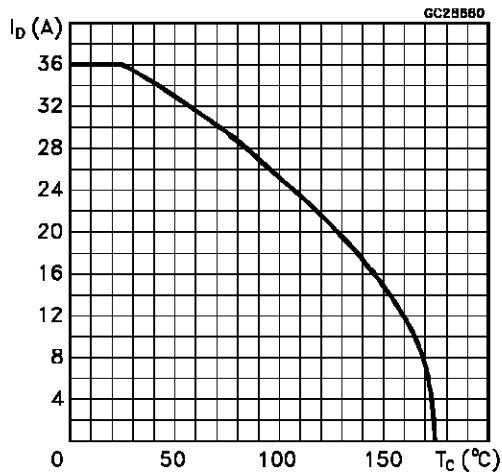
Transconductance



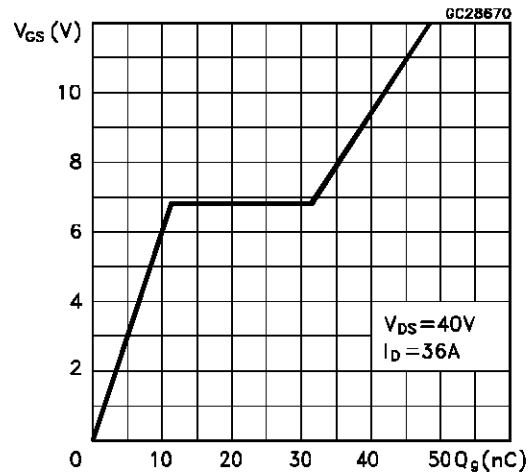
Static Drain-Source On Resistance



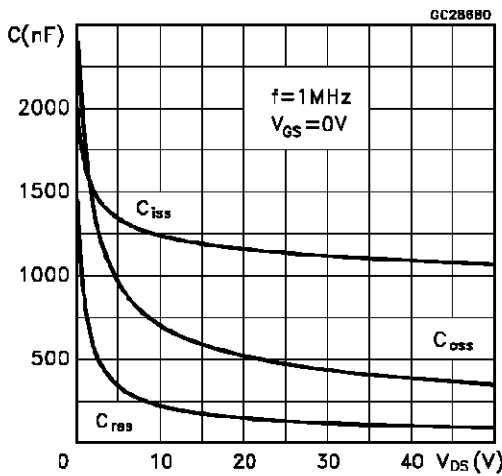
Maximum Drain Current vs Temperature



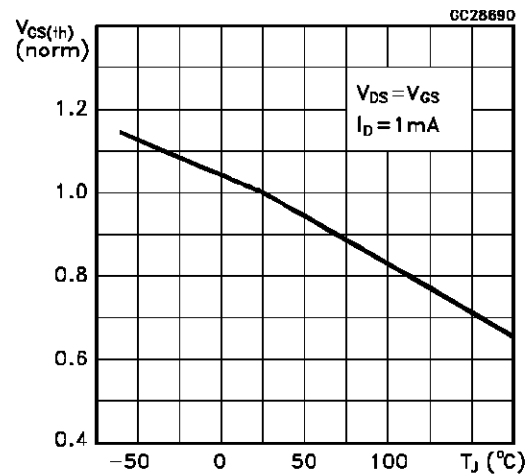
Gate Charge vs Gate-Source Voltage



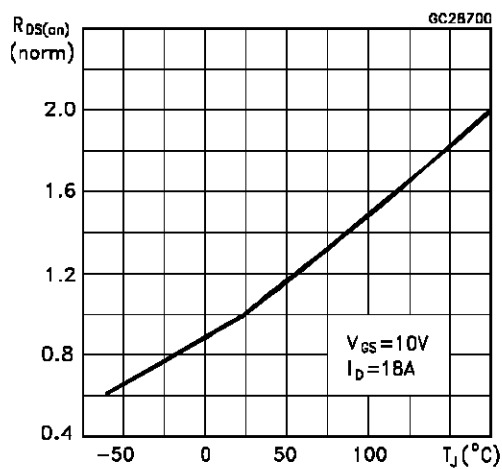
Capacitance Variation



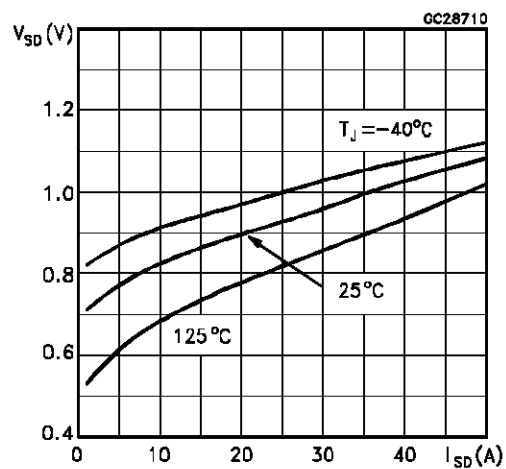
Normalized Gate Threshold Voltage vs Temperature



Normalized On Resistance vs Temperature

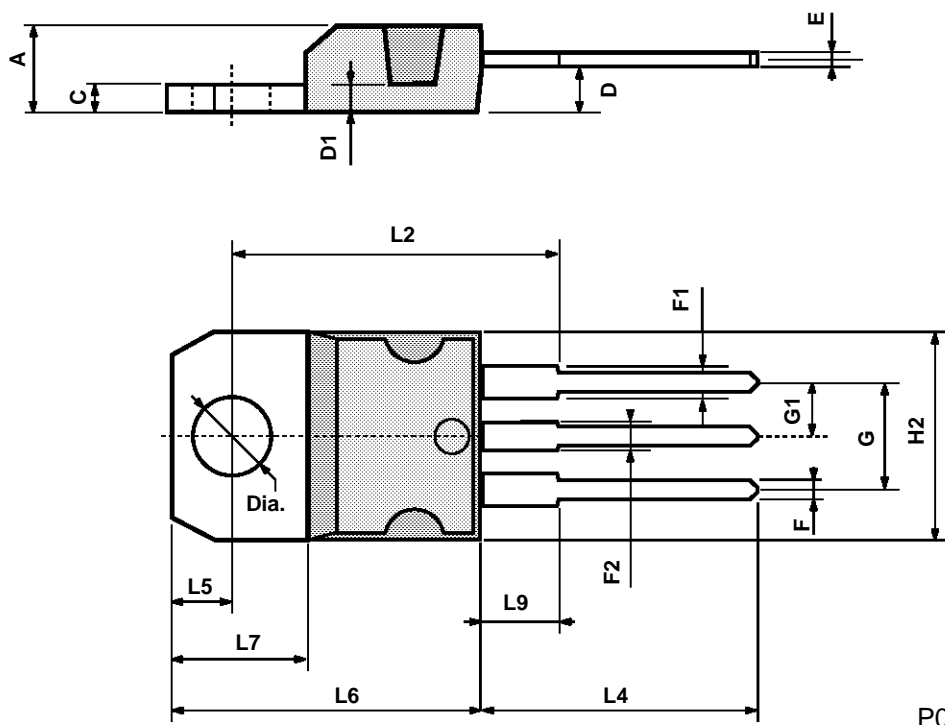


Source-Drain Diode Forward Characteristics



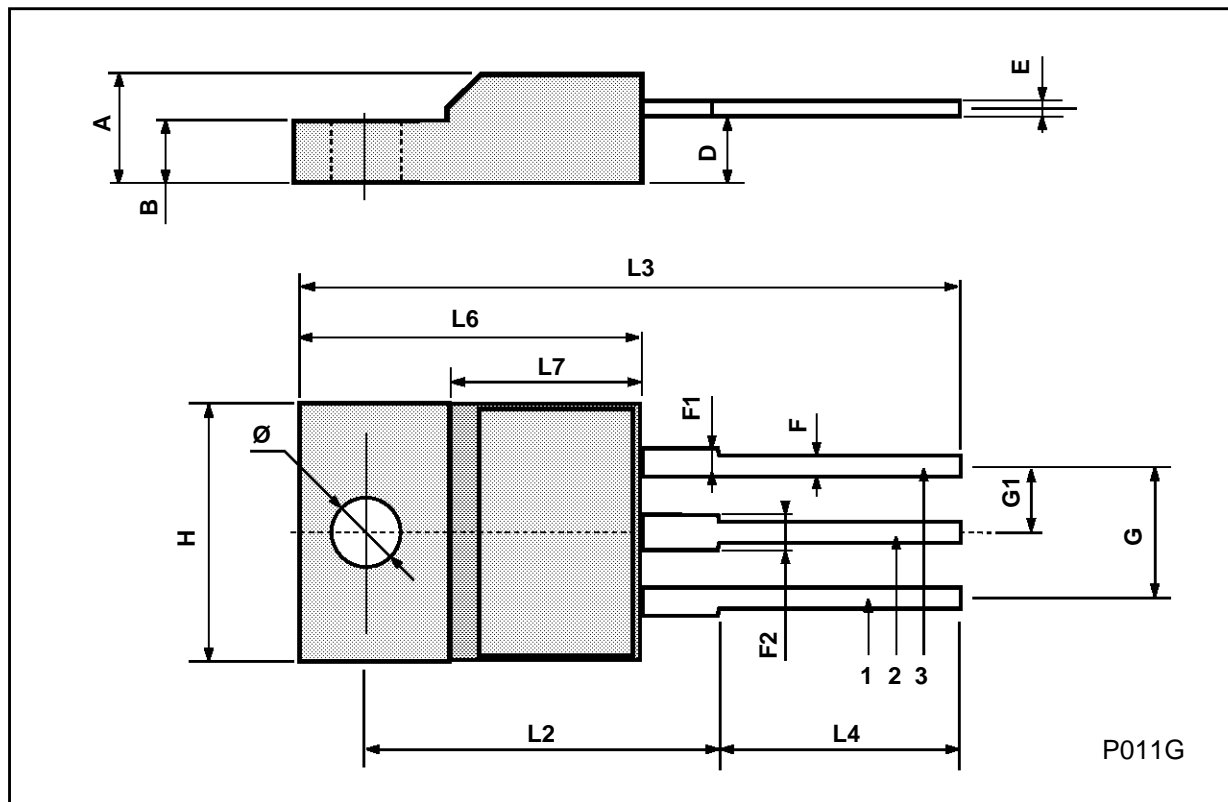
TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



ISOWATT220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.4		0.7	0.015		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	0.385		0.417
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
∅	3		3.2	0.118		0.126



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